Ordering number : ENA1564A

SANYO Semiconductors
DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

MCH3376 — General-Purpose Switching Device Applications

Features

- Low ON-resistance
- 1.8V drive
- Protection diode in

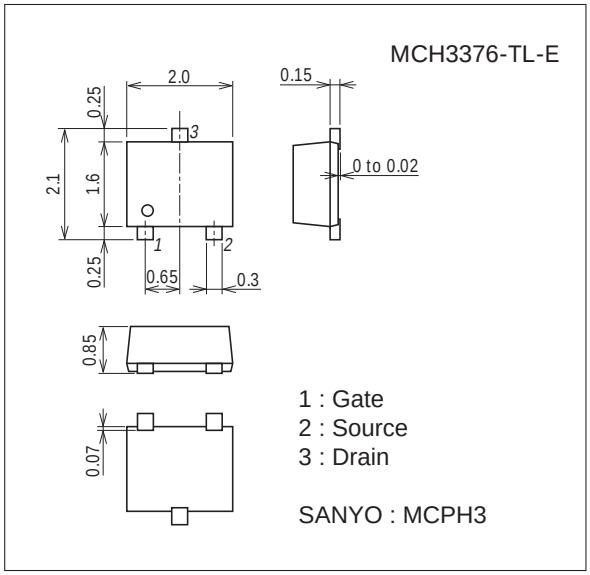
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		−20	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		−1.5	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−6	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Package Dimensions

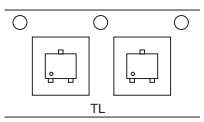
unit : mm (typ)
7019A-003



Product & Package Information

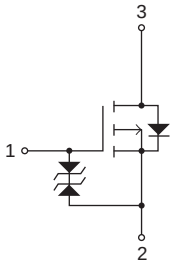
- Package : MCPH3
- JEITA, JEDEC : SC-70, SOT-323
- Minimum Packing Quantity : 3,000 pcs./reel

Packing Type: TL



Marking

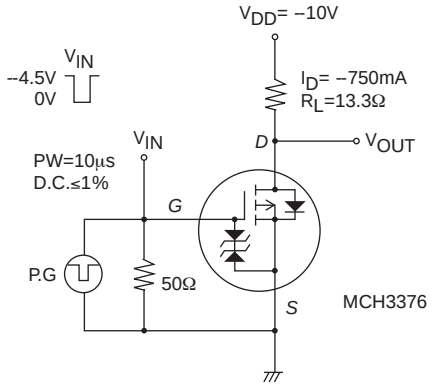
Electrical Connection



Electrical Characteristics at Ta=25°C

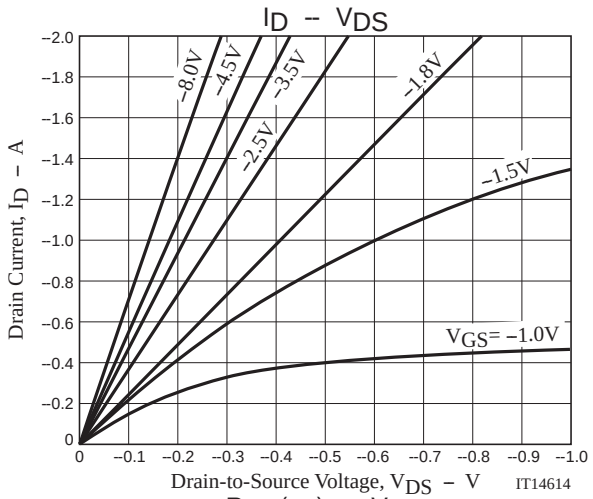
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−30V, V_{GS}=0V			−1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=−10V, I_D=−1mA	−1.2		−2.6	V
Forward Transfer Admittance	| yfs |	V_{DS}=−10V, I_D=−0.8A		1.3		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=−0.8A, V_{GS}=−10V		227	295	mΩ
	R_{DS}(on)2	I_D=−0.4A, V_{GS}=−4.5V		374	523	mΩ
	R_{DS}(on)3	I_D=−0.4A, V_{GS}=−4V		435	609	mΩ
Input Capacitance	Ciss	V_{DS}=−10V, f=1MHz		82		pF
Output Capacitance	Coss			22		pF
Reverse Transfer Capacitance	Crss			16		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		4.0		ns
Rise Time	t_r			3.3		ns
Turn-OFF Delay Time	t_d(off)			12		ns
Fall Time	t_f			5.4		ns
Total Gate Charge	Qg	V_{DS}=−15V, V_{GS}=−10V, I_D=−1.6A		2.2		nC
Gate-to-Source Charge	Qgs			0.36		nC
Gate-to-Drain “Miller” Charge	Qgd			0.49		nC
Diode Forward Voltage	V_{SD}	I_S=−1.6A, V_{GS}=0V		−0.9	−1.5	V

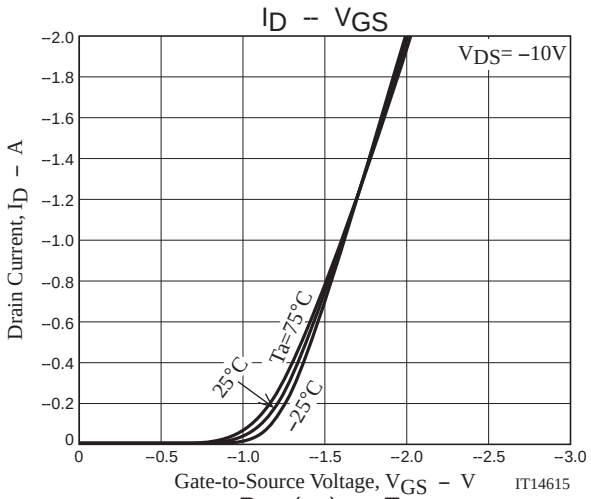
Switching Time Test Circuit

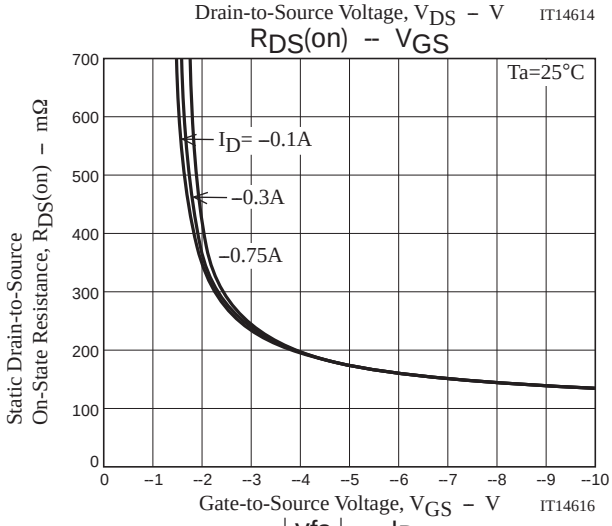


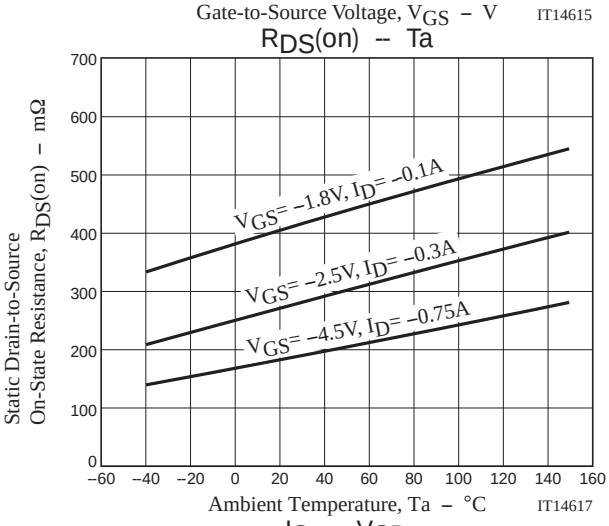
Ordering Information

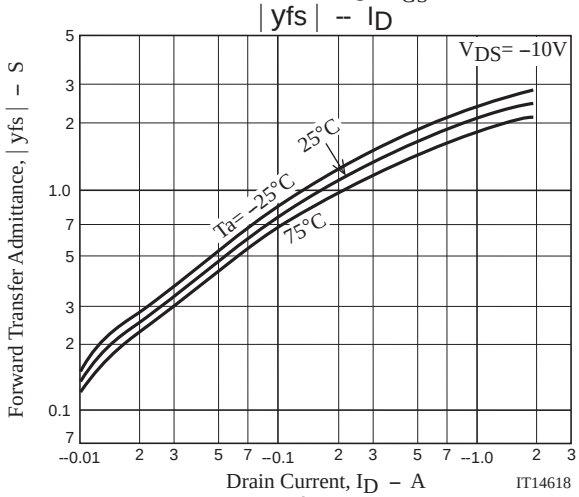
Device	Package	Shipping	memo
MCH3376-TL-E	MCPH3	3,000pcs./reel	Pb Free

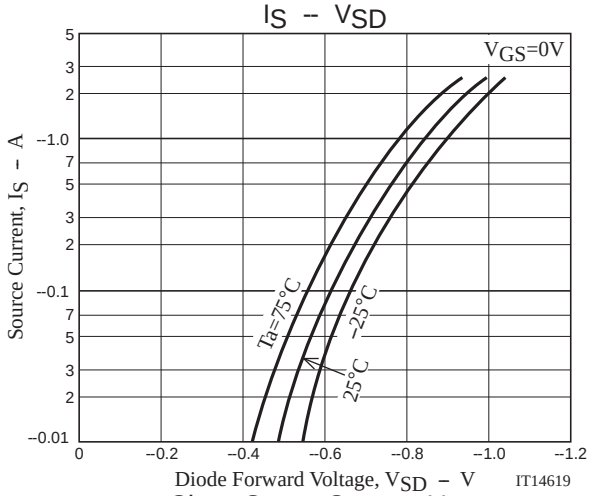

ID -- VDS
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT14614
–8.0V
–4.5V
–3.5V
–2.5V
–1.8V
–1.5V
VGS= –1.0V

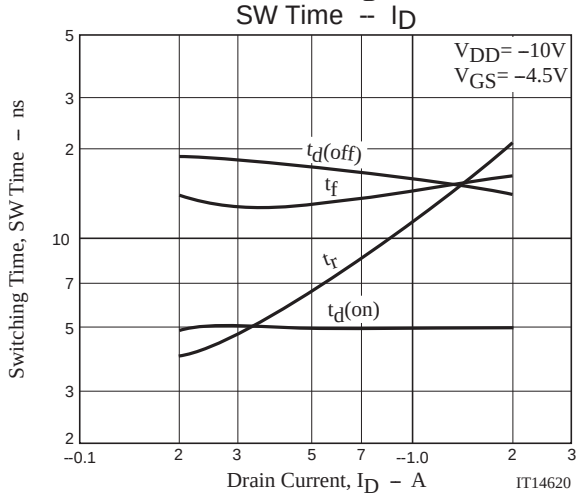

ID -- VGS
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
IT14615
VDS= –10V
25°C
Ta=75°C
–25°C

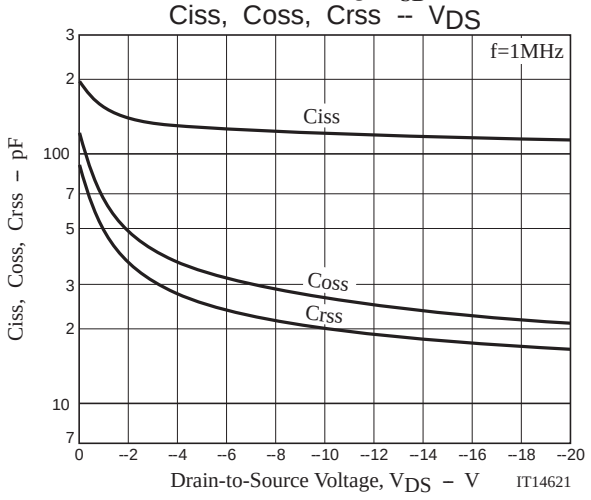

RDS(on) -- VGS
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT14616
Ta=25°C
ID= –0.1A
–0.3A
–0.75A

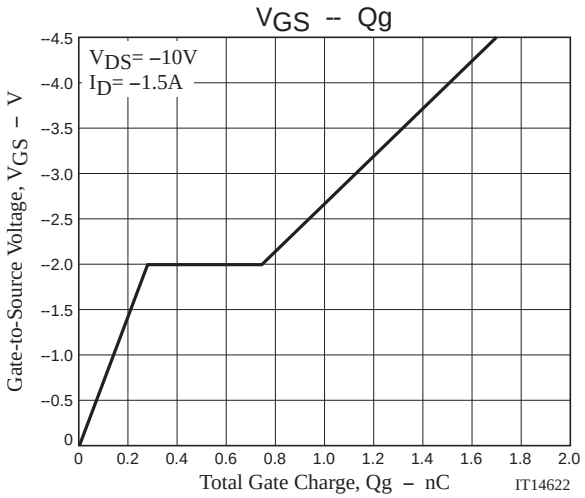

RDS(on) -- Ta
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT14617
VGS= –1.8V, ID= –0.1A
VGS= –2.5V, ID= –0.3A
VGS= –4.5V, ID= –0.75A

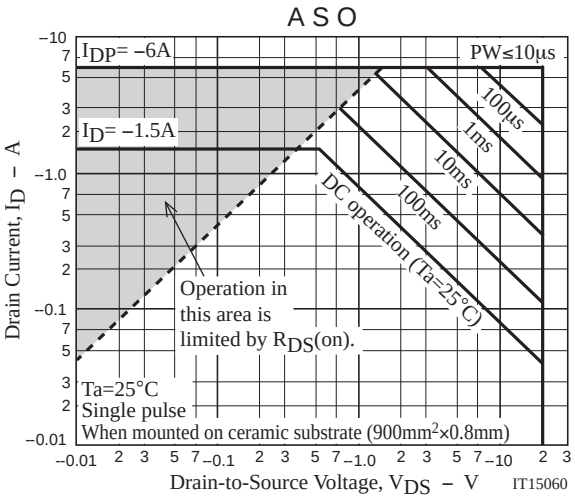

| yfs | -- ID
Forward Transfer Admittance, | yfs | – S
Drain Current, ID – A
IT14618
VDS= –10V
25°C
Ta= –25°C
75°C

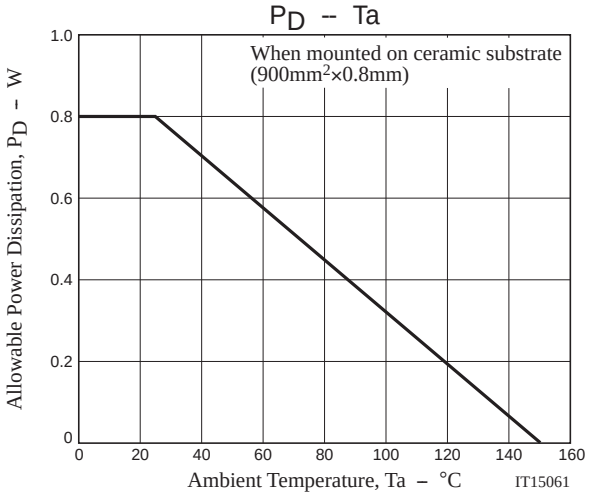

IS -- VSD
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT14619
VGS=0V
Ta=75°C
–25°C
25°C


SW Time -- ID
Switching Time, SW Time – ns
Drain Current, ID – A
IT14620
VDD= –10V
VGS= –4.5V
td(off)
tf
tr
td(on)


Ciss, Coss, Crss -- VDS
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT14621
f=1MHz
Ciss
Coss
Crss


VGS -- Qg
VDS= −10V
ID= −1.5A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT14622


A S O
IDP= −6A
PW≤10μs
ID= −1.5A
100μs
1ms
10ms
100ms
DC operation (Ta=25°C)
Operation in this area is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate (900mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT15060


PD -- Ta
When mounted on ceramic substrate (900mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT15061

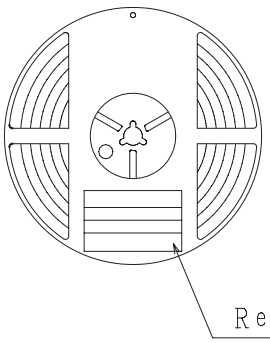
Taping Specification

MCH3376-TL-E

1. Packing Format

Package Name	Carrier Tape Type	Maximun Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
MCPH3	MCPH3	3,000	15,000	90,000	5 reels contained Dimensions:mm(external) 183×72×185	6 inner boxes contained Dimensions:mm(external) 440×195×210

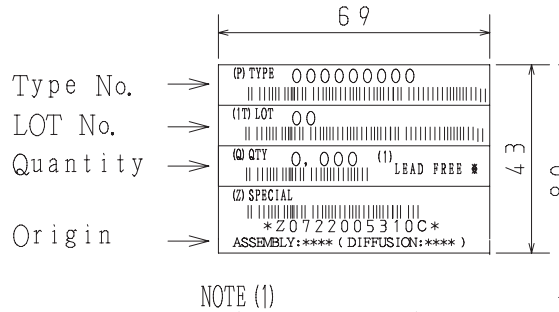
Packing method



Reel label

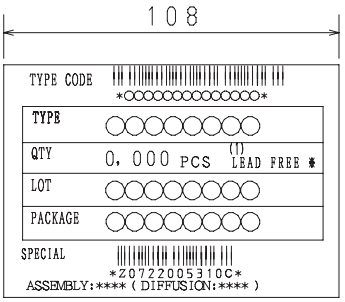
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



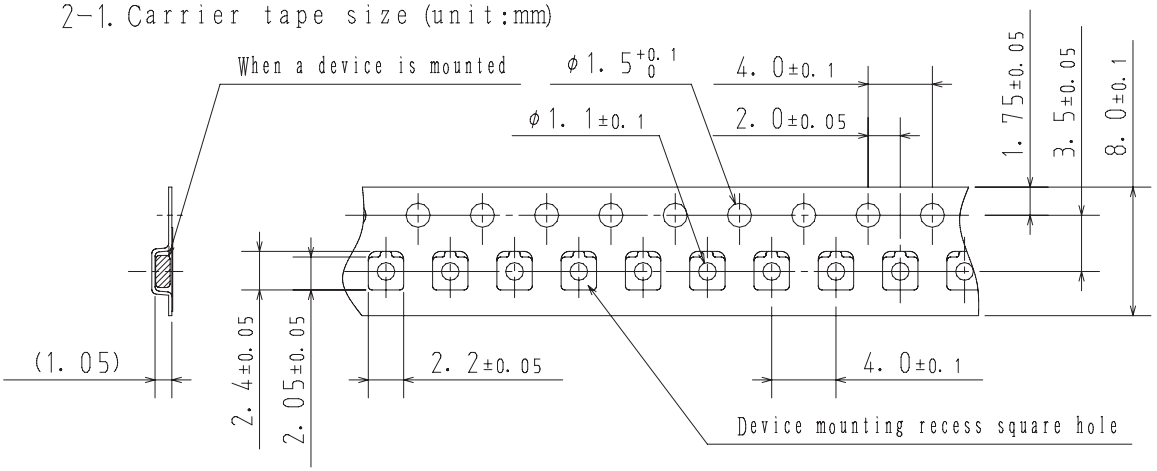
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

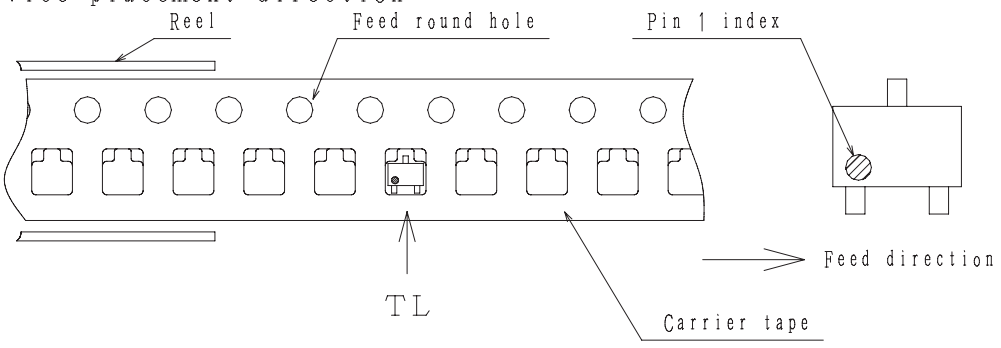
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



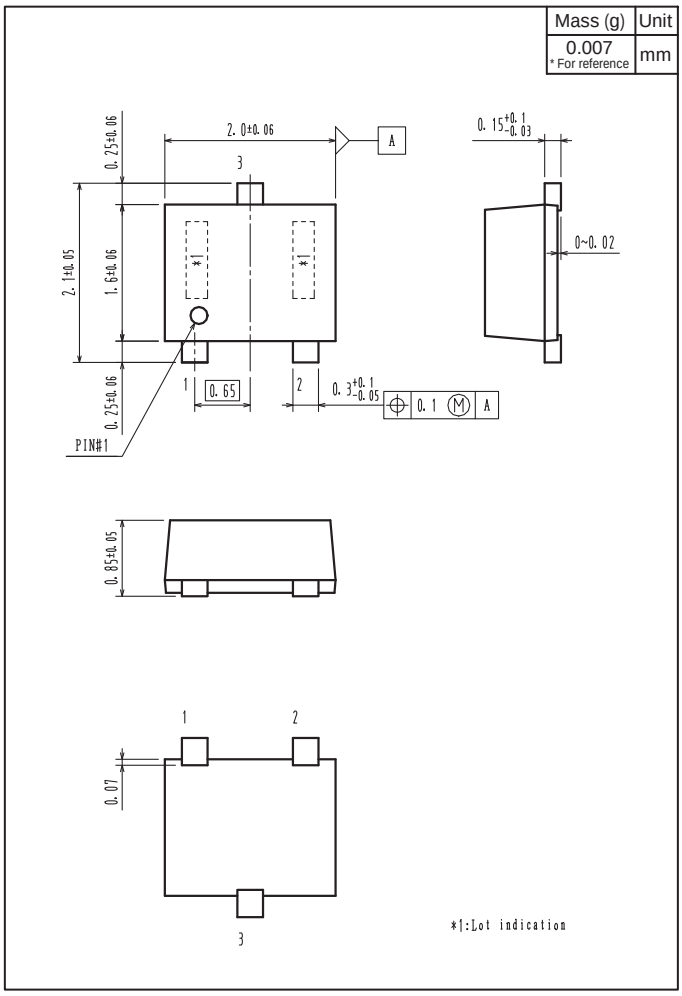
2-2. Device placement direction



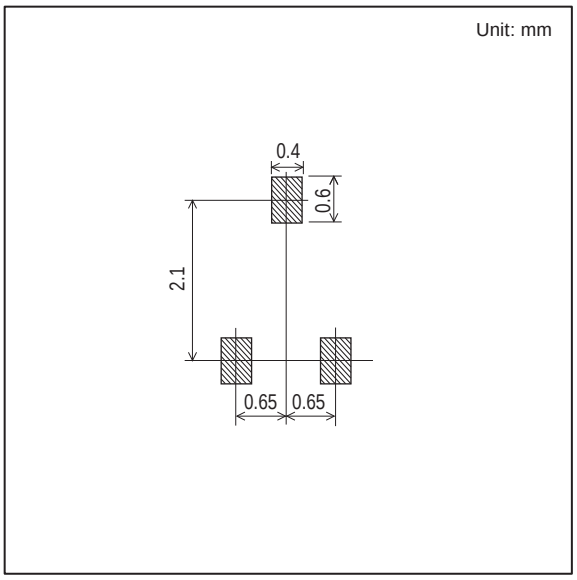
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

MCH3376-TL-E



Land Pattern Example



Note on usage : Since the MCH3376 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of June, 2012. Specifications and information herein are subject to change without notice.